

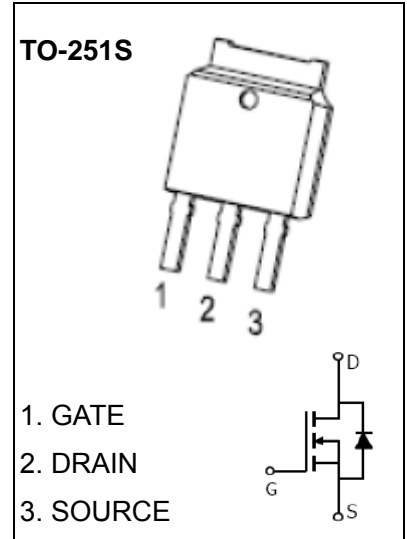


TO-251S Plastic-Encapsulate MOSFETS

CJD02N60 N-Channel Power MOSFET

General Description

The high voltage MOSFET uses an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain-to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power suppliers, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.



FEATURE

- Robust High Voltage Termination
- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- I_{DSS} and $V_{DS(on)}$ Specified at Elevated Temperature

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	2	A
Pulsed Drain Current	I_{DM}	8	
Single Pulsed Avalanche Energy*	E_{AS}	128	mJ
Power Dissipation	P_D	1.25	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	100	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-50 ~ +150	

* E_{AS} condition: $T_J=25^\circ\text{C}$, $V_{DD}=50\text{V}$, $L=64\text{mH}$, $I_{AS}=2\text{A}$, $R_G=25\Omega$, Starting $T_J = 25^\circ\text{C}$

Electrical characteristics (T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	600			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =600V, V _{GS} =0V			25	μA
		V _{DS} =480V, V _{GS} =0V, T _j =125°C			100	
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
On characteristics (note1)						
Gate-threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static drain-source on-resistance	R _{DS(on)}	V _{GS} =10V, I _D =1A		3.6	4.4	Ω
Forward transconductance	g _{FS}	V _{DS} =50V, I _D =1A	1			S
Dynamic characteristics (note 2)						
Input capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f =1MHz		435		pF
Output capacitance	C _{oss}			56		
Reverse transfer capacitance	C _{rss}			9.2		
Switching characteristics (note 2)						
Total gate charge	Q _g	V _{DS} =480V, V _{GS} =10V, I _D =2.4A		40	50	nC
Gate-source charge	Q _{gs}			4.2		
Gate-drain charge	Q _{gd}			8.4		
Turn-on delay time	t _{d(on)}	V _{DD} =300V, I _D =2A, V _{GS} =10V, R _G =18Ω		12		ns
Turn-on rise time	t _r			21		
Turn-off delay time	t _{d(off)}			30		
Turn-off fall time	t _f			24		
Drain-Source Diode Characteristics						
Drain-source diode forward voltage(note1)	V _{SD}	V _{GS} =0V, I _S =2A			1.6	V
Continuous drain-source diode forward current	I _S				2	A
Pulsed drain-source diode forward current	I _{SM}				8	A

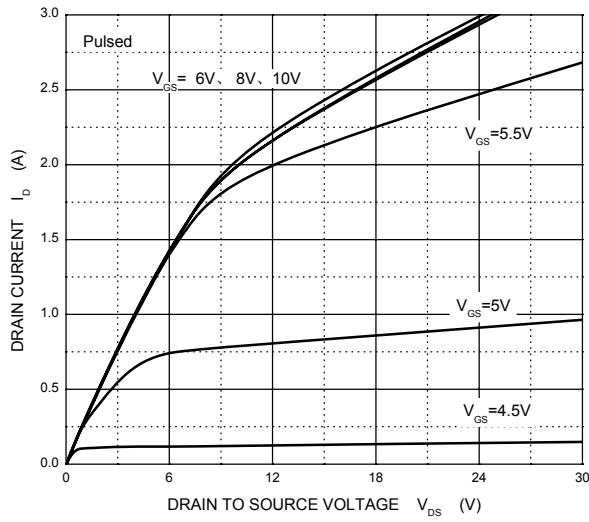
Notes:

1. Pulse Test : Pulse Width≤300μs, duty cycle ≤2%.
2. Guaranteed by design, not subject to production.

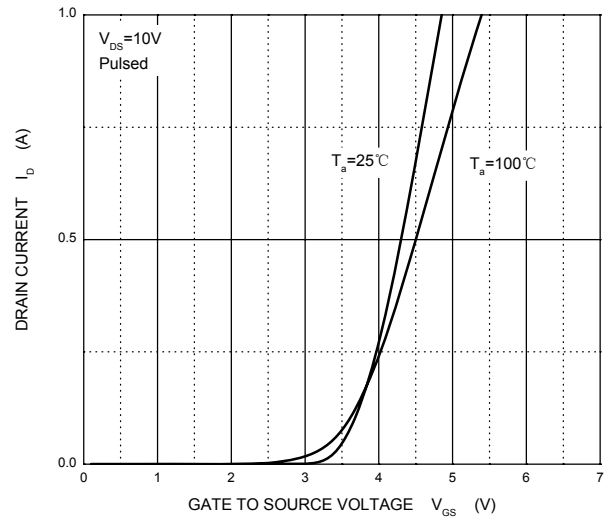
Typical Characteristics

CJD02N60

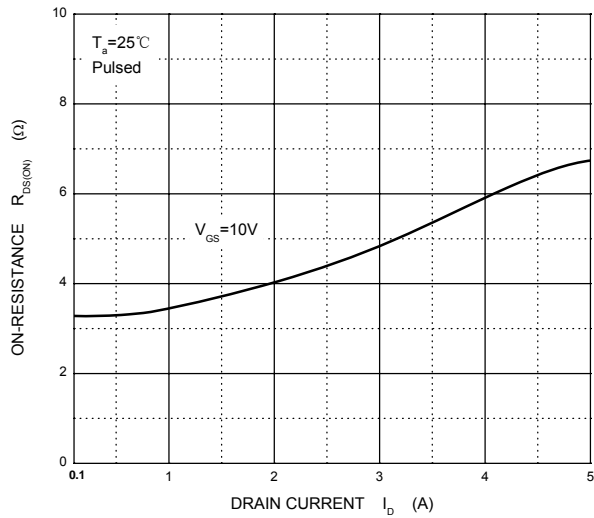
Output Characteristics



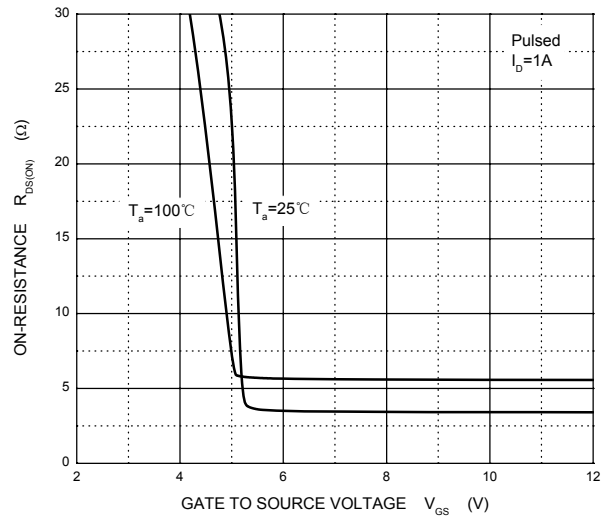
Transfer Characteristics



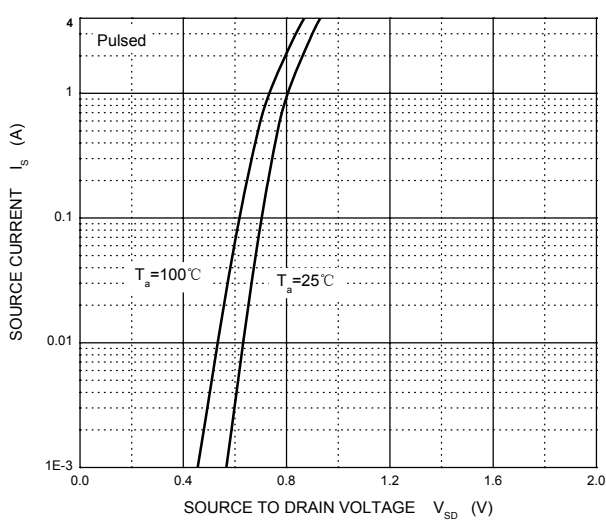
$R_{DS(ON)}$ — I_D



$R_{DS(ON)}$ — V_{GS}



I_S — V_{SD}



Threshold Voltage

